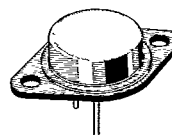
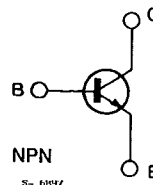


- HIGH EFFICIENCY SWITCHING
- VERY LOW SATURATION VOLTAGE AT 40A
- FAST TURN-OFF AND TURN-ON



TO-3

INTERNAL SCHEMATIC DIAGRAM

DESCRIPTION

High current, high speed transistors suited for low voltage applications : high efficiency converters, motor controls.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BUV18	BUV19	
V_{CBO}	Collector-base Voltage ($I_E = 0$)	120	160	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	60	80	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	7	7	V
I_C	Collector Current	50	50	A
I_{CM}	Collector Peak Current ($t_p < 5ms$)	90	70	A
I_B	Base Current	16	12	A
I_{BM}	Base Peak Current ($t_p < 5ms$)	40	30	A
P_{tot}	Total Dissipation at $T_c < 25^\circ C$	250		W
T_{stg}	Storage Temperature	- 65 to 200		$^\circ C$
T_j	Max. Operating Junction Temperature	200		$^\circ C$

THERMAL DATA

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$R_{thj-case}$	Thermal Resistance Junction-case	max	0.7	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

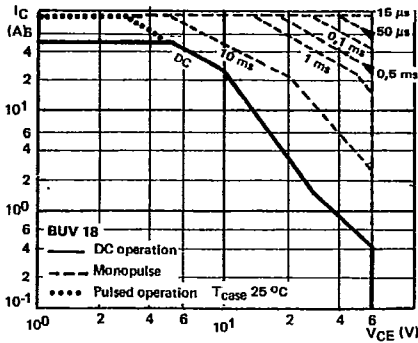
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX}	Collector Cutoff Current	$V_{CE} = V_{CEX}$ $V_{BE} = -1.5\text{V}$ $V_{CE} = V_{CEX}$ $V_{BE} = -1.5\text{V}$ $T_c = 100^{\circ}\text{C}$			1 3	mA mA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 5\text{V}$			1	mA
$V_{CE0(sus)}^*$	Collector-Emitter Sustaining Voltage	$I_C = 0.2\text{A}$ $L = 25\text{mH}$ for BUV18 for BUV19	60 80			V V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	$I_E = 50\text{mA}$	7			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 40\text{A}$ $I_B = 4\text{A}$ for BUV18 $I_C = 80\text{A}$ $I_B = 8\text{A}$ for BUV18 $I_C = 30\text{A}$ $I_B = 3\text{A}$ for BUV19 $I_C = 60\text{A}$ $I_B = 6\text{A}$ for BUV19			0.6 1.5 0.6 1.2	V V V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 80\text{A}$ $I_B = 8\text{A}$ for BUV18 $I_C = 60\text{A}$ $I_B = 6\text{A}$ for BUV19			2.2 2	V V
f_T	Transition Frequency	$f = 10\text{MHz}$ $V_{CE} = 15\text{A}$ $I_C = 2\text{A}$	8			MHz

RESISTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_{on}	Turn-on Time	for BUV18 $V_{CC} = 60\text{V}$ $I_C = 80\text{A}$		1.2	1.5	μs
t_s	Storage Time			0.6	1.1	μs
t_f	Fall Time	$I_{B1} = -I_{B2} = 8\text{A}$		0.18	0.25	μs
t_s	Storage Time	for BUV18 $V_{CC} = 60\text{V}$ $I_C = 80\text{A}$			1.7	μs
t_f	Fall Time	$I_{B1} = -I_{B2} = 8\text{A}$ $T_c = 125^{\circ}\text{C}$			0.5	μs
t_{on}	Turn-on Time	for BUV19 $V_{CC} = 80\text{V}$ $I_C = 60\text{A}$		0.9	1.3	μs
t_s	Storage Time			0.6	1.1	μs
t_f	Fall Time	$I_{B1} = -I_{B2} = 6\text{A}$		0.17	0.25	μs
t_s	Storage Time	for BUV19 $V_{CC} = 80\text{V}$ $I_C = 60\text{A}$			1.7	μs
t_f	Fall Time	$I_{B1} = -I_{B2} = 6\text{A}$ $T_c = 125^{\circ}\text{C}$			0.5	μs

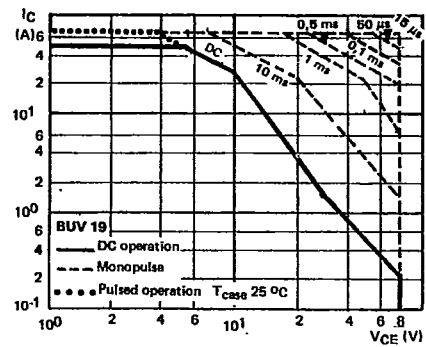
* Pulsed : Pulse duration = 300 μs , duty cycle = 2%

DC and AC Pulse Area.

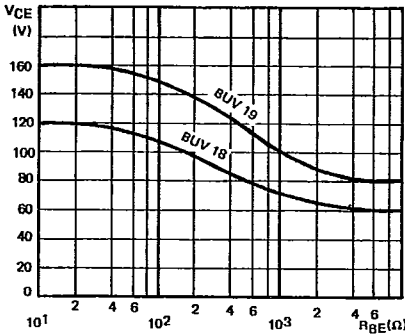


DC and AC Pulse Area.

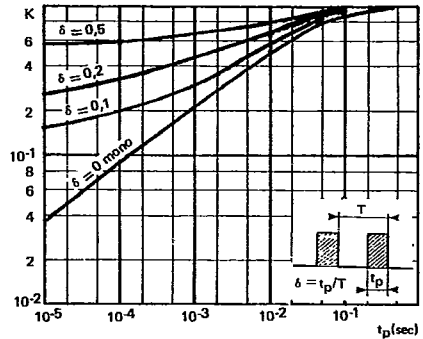
T-33-15



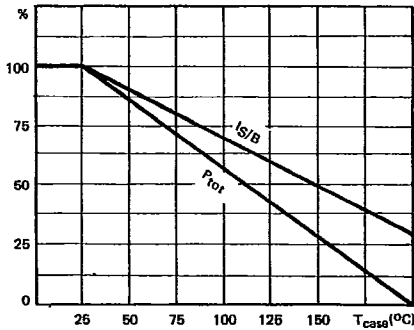
Collector-emitter Voltage vs. Base-emitter Resistance.



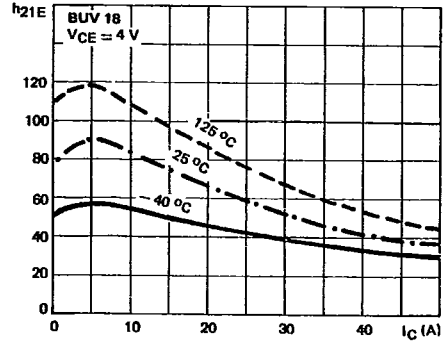
Transient Thermal Response.



Power and $I_{S/B}$ Derating vs. Case Temperature.



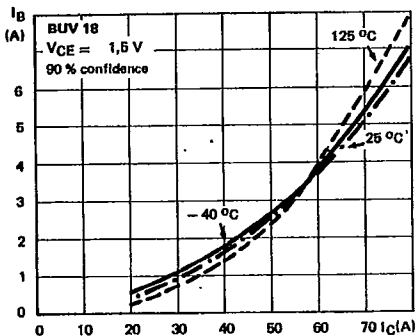
DC Current Gain.



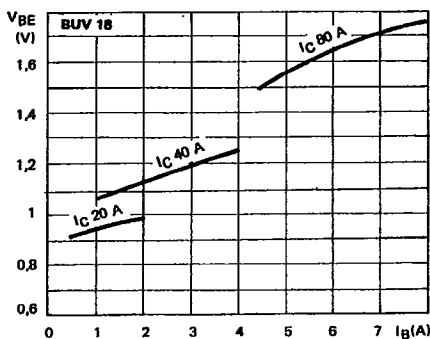
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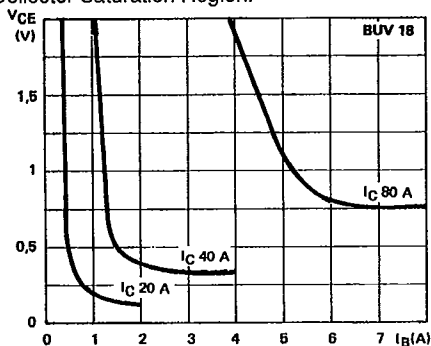
Minimum Base Current to Saturate the Transistor.



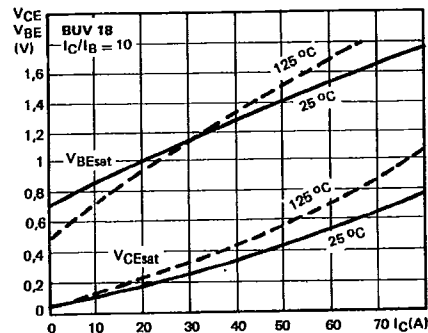
Base Characteristics.



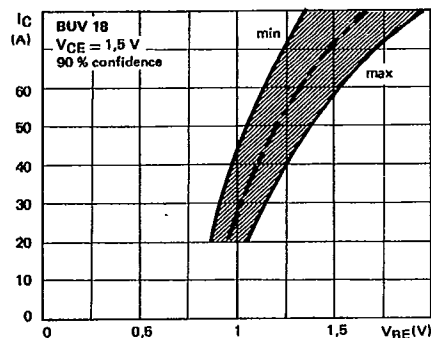
Collector Saturation Region.



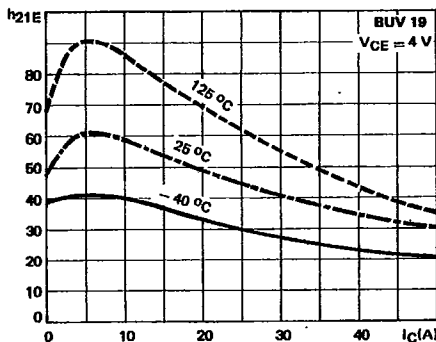
Saturation Voltage.



Collector Current Spread vs Base Emitter Voltage.



DC Current Gain.

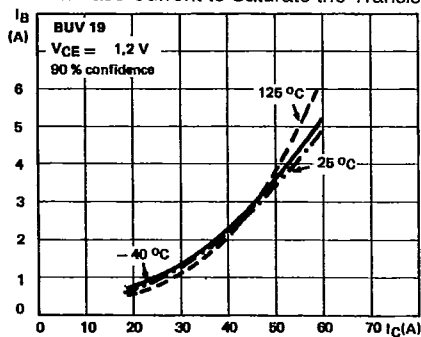


S G S-THOMSON

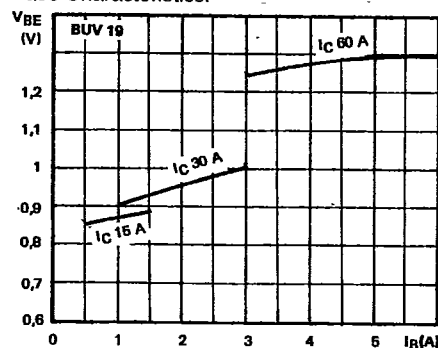
30E D

T-33-15

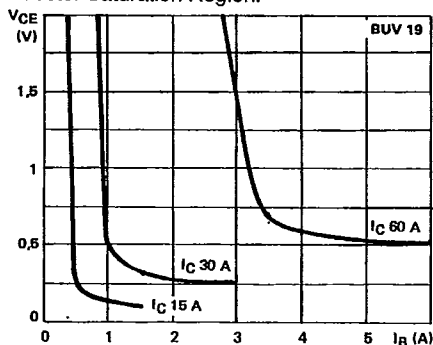
Minimum Base Current to Saturate the Transistor.



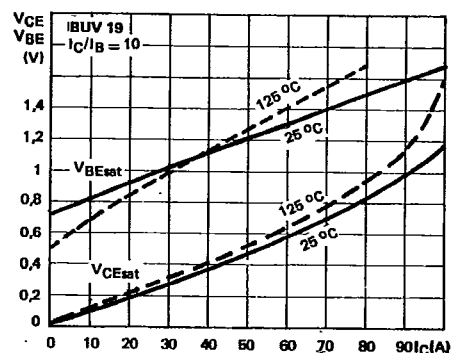
Base Characteristics.



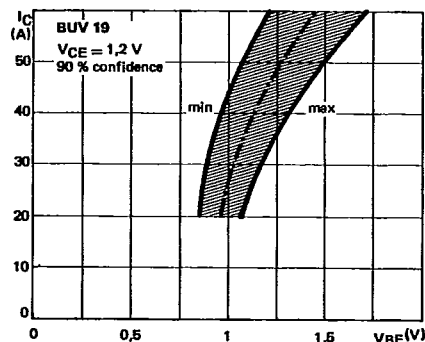
Collector Saturation Region.



Saturation Voltage.



Collector Current Spread vs Base Emitter Voltage.



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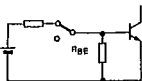
30E D

SWITCHING OPERATING AND OVERLOAD AREAS

T-33-15

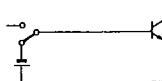
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3DE D



Transistor Forward Biased

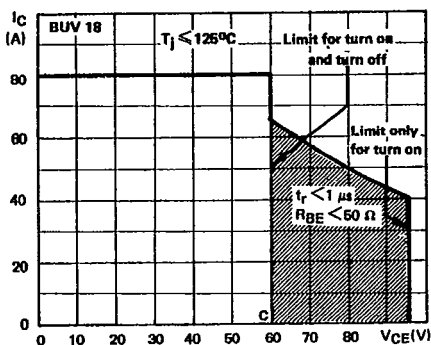
- During the turn on
- During the turn off without negative base-emitter voltage and $R_{BE} \geq 3 \Omega$



Transistor Reverse Biased

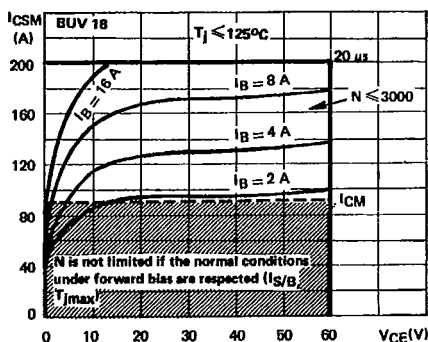
- During the turn off with negative base emitter voltage

Forward Biased Safe Operating Area (FBSOAR).



The hatched zone can only be used for turn on.

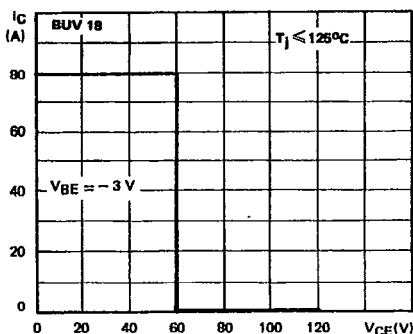
Forward Biased Accidental Overload Area (FBAOA).



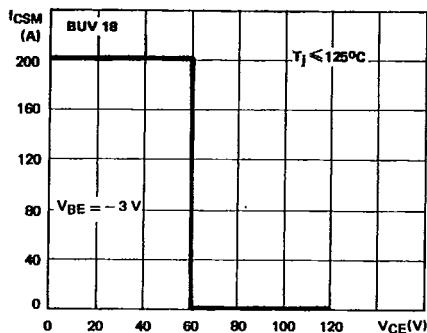
The Kellogg network (heavy print) allows the calculation of the maximum value of the short-circuit current for a given base current I_B (90 % confidence).

High accidental surge currents ($I > I_{CM}$) are allowed if they are non repetitive and applied less than 3000 times during the component life.

Reverse Biased Safe Operating Area (RBSOAR).



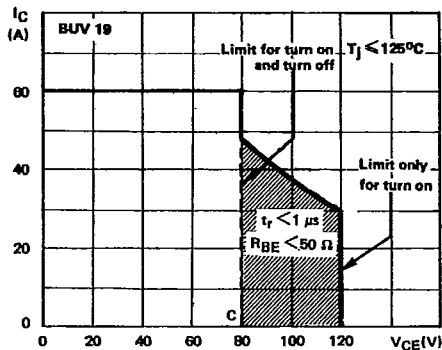
Reverse Biased Accidental Overload Area (RBAOA).



After the accidental overload current, the RBAOA has to be used for the turn off.

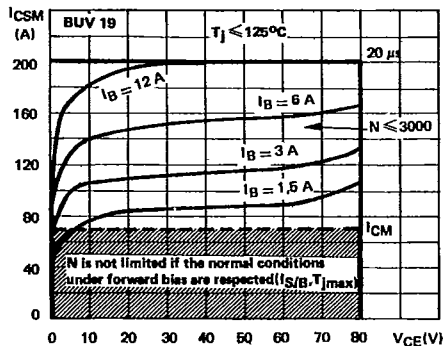
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Forward Biased Safe Operating Area (FBSOAR).



The hatched zone can only be used for turn on.

Forward Biased Accidental Overload Area (FBAOA).

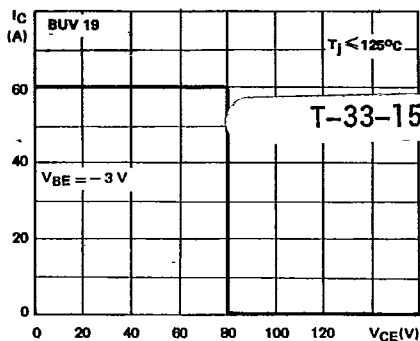


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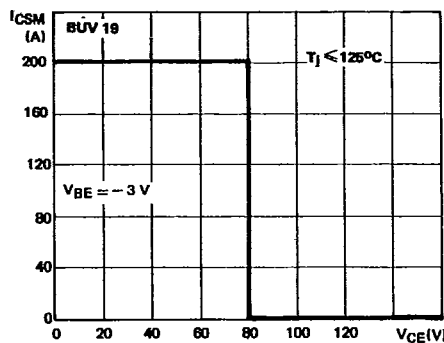
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30E D

Reverse Biased Safe Operating Area (RBSOAR).



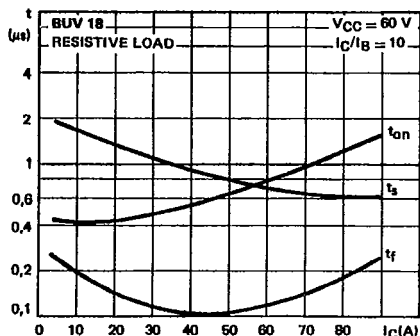
Reverse Biased Accidental Overload



After the accidental overload current, the RBAOA has to be used for the turn off.

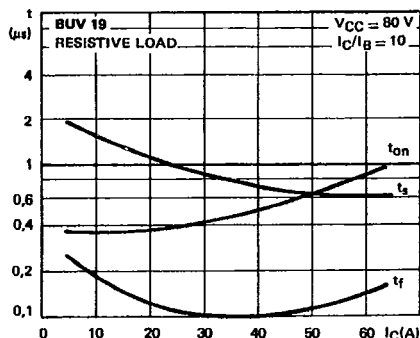
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Switching Times vs Collector Current (resistive load).

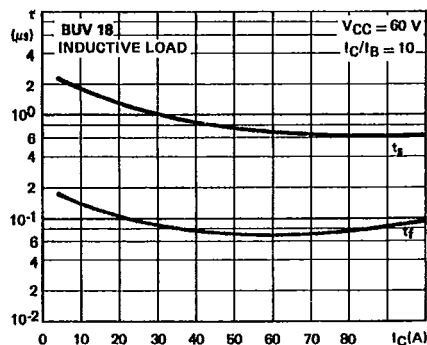


3DE D

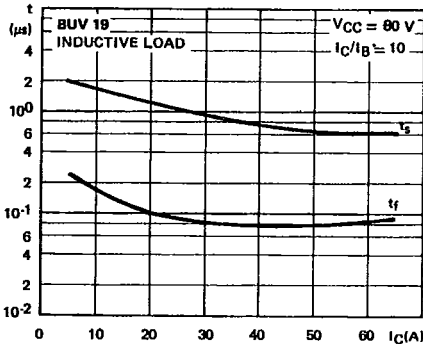
Switching Times vs Collector Current (resistive load).



Switching Times vs Collector Current.



Switching Times vs Collector Current.



Switching Times vs Junction Temperature.

